	L #	Hits	Search Text	DBs
1	L1	166687	"438"/$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
2	L2	1177	1 and (feRAM or (ferroelectric near (memory or device)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
3	L3	47	2 and glue near (layer or film)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
4	L4	7	3 and (remov$3 or etch$3) near barrier	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
5	L5	52	(choi-eun-seok or yeom-seung-jin).in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
6	L6	11	5 and glue near (layer or film)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
7	L7	3439	(feRAM or (ferroelectric near (memory or device))).ti.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
8	L8	37	7 and (remov$3 or etch$3) near barrier	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
9	L9	1	8 and glue near (layer or film)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
10	L10	8946	(feRAM or (ferroelectric near (memory or device)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
11	L11	2379	10 and ((upper and lower) or (top and bottom)) near electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
12	L12	914	11 and barrier near (layer or film)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
13	L13	41	12 and glue near (layer or film)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
14	L14	12	13 and (remov$3 or etch$3) near barrier	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB